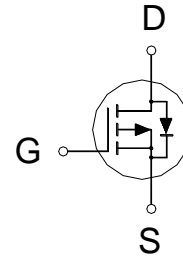


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-20V	65mΩ	-15A

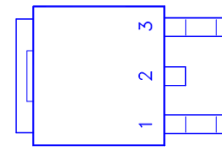


Features

- Pb-Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.

Applications

- Protection Circuits Applications.
- Logic/Load Switch Circuits Applications.



1. GATE
2. DRAIN
3. SOURCE

100% UIS Tested
100% Rg Tested

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ °C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±10	V
Continuous Drain Current ³	$T_C = 25\text{ °C}$	I_D	-15	A
	$T_C = 100\text{ °C}$		-9.8	
Pulsed Drain Current ¹		I_{DM}	-30	
Avalanche Current		I_{AS}	-11	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	6	mJ
Power Dissipation	$T_C = 25\text{ °C}$	P_D	25	W
	$T_C = 100\text{ °C}$		10	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		5	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

¹Pulse width limited by maximum junction temperature.

²Package limitation current is -10A.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

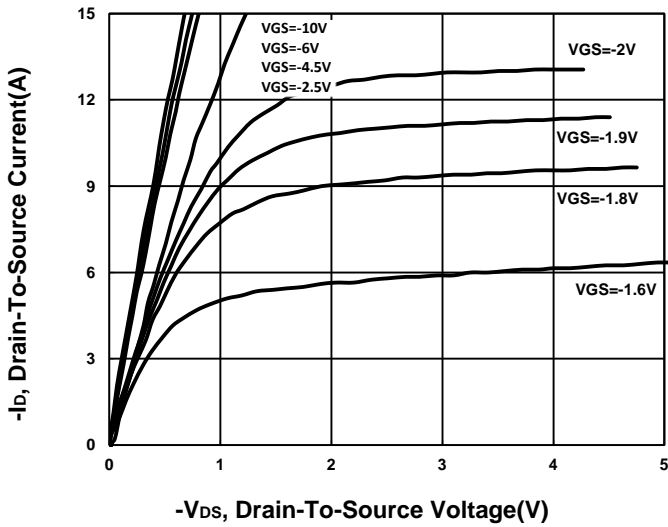
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.3	-0.7	-1	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±10V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -16V, V _{GS} = 0V			-1	μA
		V _{DS} = -10V, V _{GS} = 0V, T _J = 125 °C			-10	
Drain-Source On-State Resistance ¹	R _{DSON}	V _{GS} = -4.5V, I _D = -2.5A		50	65	mΩ
		V _{GS} = -2.5V, I _D = -2A		63	85	
		V _{GS} = -1.8V, I _D = -1A		82	120	
Forward Transconductance ¹	g _{fs}	V _{DS} = -5V, I _D = -2.5A		11		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -10V, f = 1MHz		576		pF
Output Capacitance	C _{oss}			66		
Reverse Transfer Capacitance	C _{rss}			50		
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		8		Ω
Total Gate Charge ²	Q _g (V _{GS} =-4.5V)	V _{DS} = -10V, I _D = -2.5A		6.7		nC
	Q _g (V _{GS} =-2.5V)			4		
Gate-Source Charge ²	Q _{gs}			0.8		
Gate-Drain Charge ²	Q _{gd}			1.8		
Turn-On Delay Time ²	t _{d(on)}		V _{DS} = -10V, I _D ≅ -2.5A, V _{GS} = -4.5V, R _{GEN} = 6Ω		16	
Rise Time ²	t _r			37		
Turn-Off Delay Time ²	t _{d(off)}			52		
Fall Time ²	t _f			60		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current ³	I _S				-20	A
Forward Voltage ¹	V _{SD}	I _F = -2.5A, V _{GS} = 0V			-1.2	V
Reverse Recovery Time	t _{rr}	I _F = -2.5A, dI _F /dt = 100A / μS		7		nS
Reverse Recovery Charge	Q _{rr}			1		nC

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

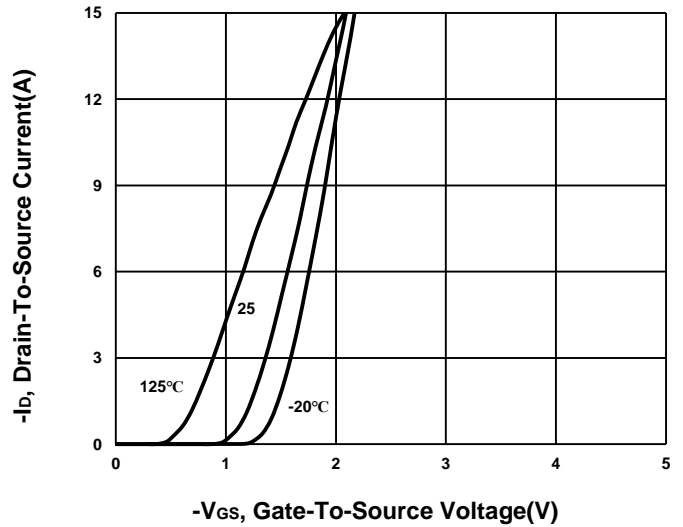
²Independent of operating temperature.

³Package limitation current is -10A.

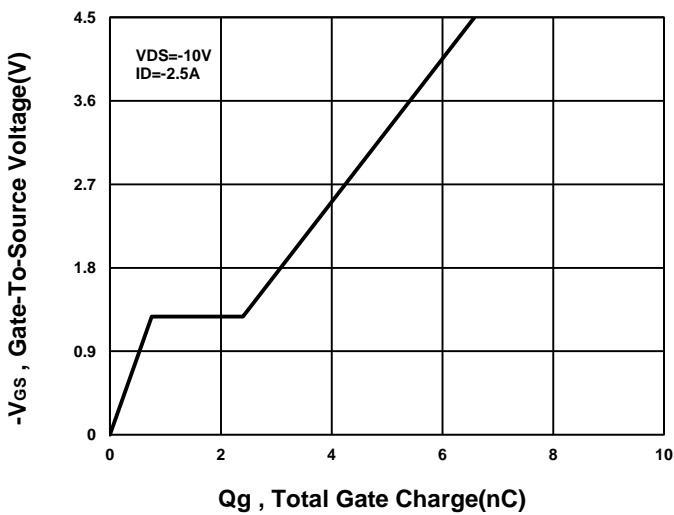
Output Characteristics



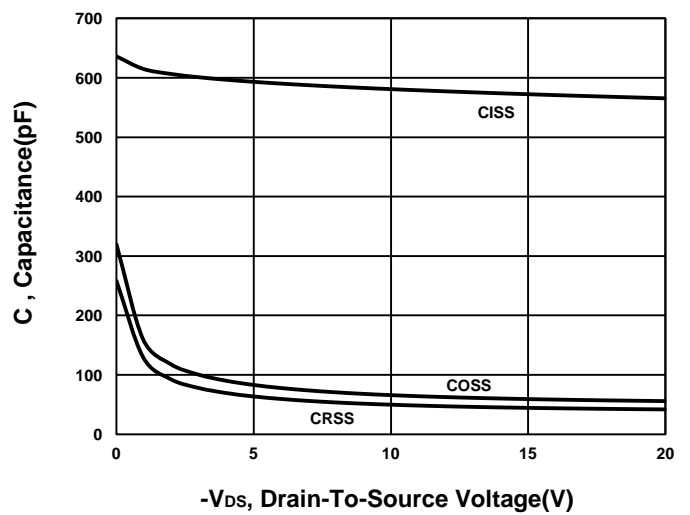
Transfer Characteristics



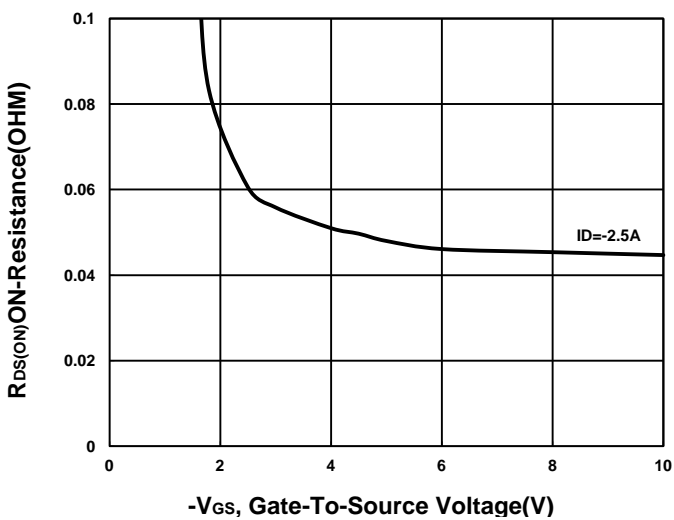
Gate charge Characteristics



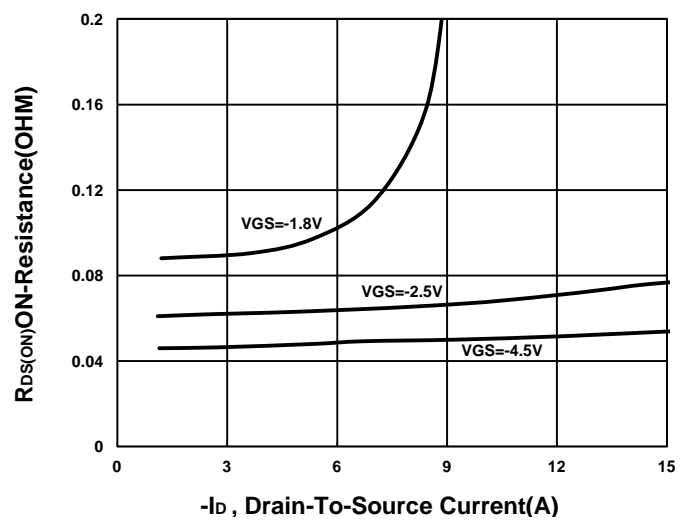
Capacitance Characteristic



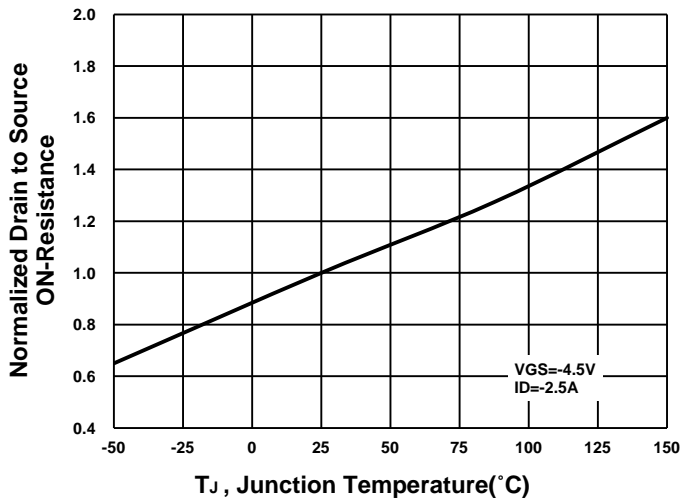
On-Resistance VS Gate-To-Source



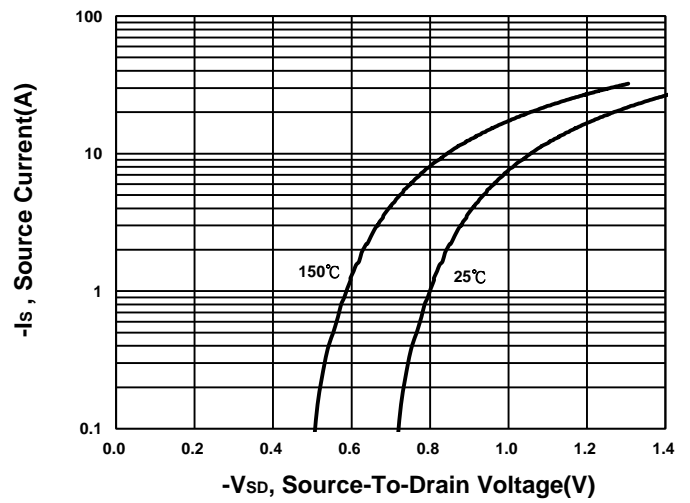
On-Resistance VS Drain Current



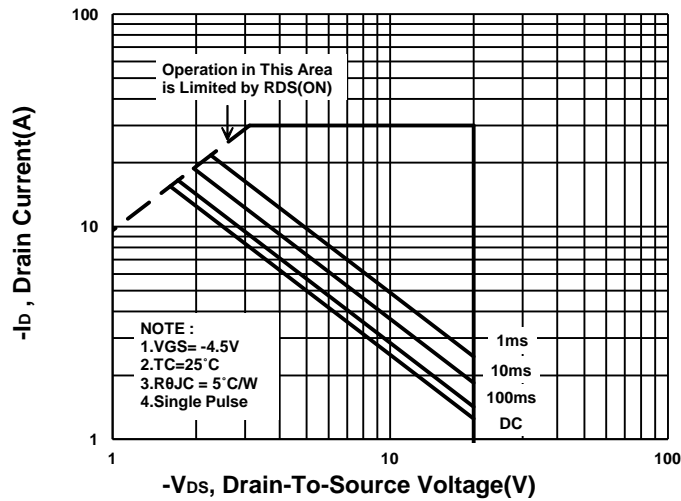
On-Resistance VS Temperature



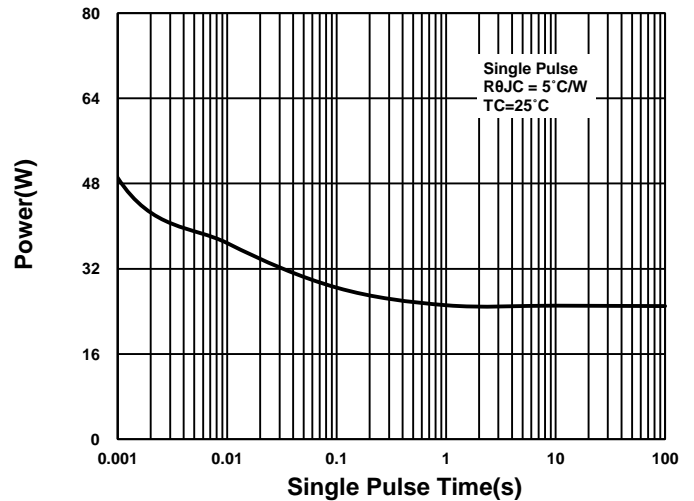
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

